### 2.5V Drive Nch+Nch MOS FET

## EM6K1

## - Structure

Silicon N-channel MOS FET

## -Features

1) Two 2 SK3019 transistors in a single EMT package.
2) The MOS FET elements are independent, eliminating mutual interference.
3) Mounting cost and area can be cut in half.
4) Low on-resistance.
5) Low voltage drive ( 2.5 V ) makes this device ideal for portable equipment.

## - Applications

Interfacing, switching (30V, 100mA)
-Packaging specifications

| Type | Package | Taping |
| :--- | :--- | :---: |
|  | Code | T2R |
|  | Basic ordering unit <br> (pieces) | 8000 |
| EM6K1 | $\bigcirc$ |  |

- Absolute maximum ratings $\left(\mathrm{Ta}=25^{\circ} \mathrm{C}\right)$
<tt is the same ratings for $\operatorname{Tr} 1$ and $\operatorname{Tr} 2 .>$

| Parameter | Symbol | Limits | Unit |  |
| :--- | :---: | :---: | :---: | :---: |
| Drain-source voltage | Voss | 30 | V |  |
| Gate-source voltage | VGss | $\pm 20$ | V |  |
| Drain current | Continuous | ID | $\pm 100$ | mA |
|  | Pulsed | $\mathrm{IDP}^{* 1}$ | $\pm 400$ | mA |
| Total power dissipation | $\mathrm{PD}^{* 2}$ | 150 | $\mathrm{~mW} / \mathrm{TOTAL}$ |  |
|  |  | 120 | $\mathrm{~mW} / \mathrm{ELEMENT}$ |  |
| Channel temperature | Tch | 150 | ${ }^{\circ} \mathrm{C}$ |  |
| Storage temperature | Tstg | $-55 \mathrm{to}+150$ | ${ }^{\circ} \mathrm{C}$ |  |
| *1 PW$\leq 10$ us, Duty cycle $\leq 1 \%$ |  |  |  |  |

*1 Pw $\leq 10 \mu \mathrm{~s}$, Duty cycle $1 \%$

[^0]-External dimensions (Unit : mm)


- Equivalent circuit


Transistor
-Electrical characteristics ( $\mathrm{Ta}=25^{\circ} \mathrm{C}$ )
<lt is the same characteristics for Tr1 and Tr2.>

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Gate-source leakage | Igss | - | - | $\pm 1$ | $\mu \mathrm{A}$ | VGs $= \pm 20 \mathrm{~V}, \mathrm{VdS}=0 \mathrm{~V}$ |
| Drain-source breakdown voltage | $V_{\text {(BR) }}$ DSS | 30 | - | - | V | $\mathrm{ld}=10 \mu \mathrm{~A}, \mathrm{VGS}=0 \mathrm{~V}$ |
| Zero gate voltage drain current | Idss | - | - | 1.0 | $\mu \mathrm{A}$ | Vds $=30 \mathrm{~V}$, VGgs $=0 \mathrm{~V}$ |
| Gate threshold voltage | VGS(th) | 0.8 | - | 1.5 | V | V $\mathrm{dS}=3 \mathrm{~V}, \mathrm{ld}=100 \mu \mathrm{~A}$ |
| Static drain-source on-starte resistance | Rds(on) | - | 5 | 8 | $\Omega$ | $\mathrm{ld}=10 \mathrm{~mA}, \mathrm{VGs}=4 \mathrm{~V}$ |
|  | Rds(on) | - | 7 | 13 | $\Omega$ | $\mathrm{ld}=1 \mathrm{~mA}, \mathrm{VGs}=2.5 \mathrm{~V}$ |
| Forward transfer admittance | \| $\mathrm{Yfs}_{\text {f }}$ \| | 20 | - | - | mS | V $\mathrm{DS}=3 \mathrm{~V}, \mathrm{ID}=10 \mathrm{~mA}$ |
| Input capacitance | Ciss | - | 13 | - | pF | $\begin{aligned} & \mathrm{VDS}=5 \mathrm{~V} \\ & \mathrm{VGS}=0 \mathrm{~V} \\ & \mathrm{f}=1 \mathrm{MHz} \end{aligned}$ |
| Output capacitance | Coss | - | 9 | - | pF |  |
| Reverse transfer capacitance | Crss | - | 4 | - | pF |  |
| Turn-on delay time | td(on) | - | 15 | - | ns | $\begin{aligned} & \mathrm{I}_{\mathrm{D}}=10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{DD}} \fallingdotseq 5 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{GS}}=5 \mathrm{~V} \\ & \mathrm{R}_{\mathrm{L}}=500 \Omega \\ & \mathrm{R}_{\mathrm{G}}=10 \Omega \end{aligned}$ |
| Rise time | tr | - | 35 | - | ns |  |
| Turn-off delay time | td(off) | - | 80 | - | ns |  |
| Fall time | tf | - | 80 | - | ns |  |

## -Electrical characteristic curves



Fig. 1 Typical Output Characteristics


GATE-SOURCE VOLTAGE: VGS (V)
Fig. 2 Typical Transfer Characteristics


Fig. 3 Gate Threshold Voltage vs. Channel Temperature


Fig. 4 Static Drain-Source On-State Resistance vs. Drain Current (I)


Fig. 5 Static Drain-Source On-State Resistance vs. Drain Current (II)


Fig. 6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage


Fig. 7 Static Drain-Source On-State
Resistance vs.
Channel Temperature


Fig. 8 Forward Transfer Admittance vs. Drain Current


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage (I)


Fig. 10 Reverse Drain Current vs. Source-Drain Voltage (II)


Fig. 11 Typical Capacitance vs. Drain-Source Voltage


Fig. 12 Switching Characteristics

- Switching characteristics measurement circuits


Fig. 13 Switching Time Test Circuit


Fig. 14 Switching Time Waveforms

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[^0]:    *2 With each pin mounted on the recommended lands.

